BF493S

High Voltage Transistor

PNP Silicon

Features

• This is a Pb-Free Device*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-350	Vdc
Collector - Base Voltage	V _{CBO}	-350	Vdc
Emitter-Base Voltage	V _{EBO}	-6.0	Vdc
Collector Current – Continuous	I _C	-500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above = 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

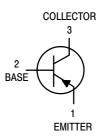
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

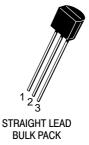
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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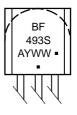
http://onsemi.com





TO-92 CASE 29 STYLE 1

MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
BF493SG	TO-92 (Pb-Free)	5000 Units / Bulk

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BF493S

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•	•	
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	-350	-	Vdc
Collector – Base Breakdown Voltage $(I_C = -100 \mu Adc, I_E = 0)$	V _(BR) CBO	-350	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = -100 \mu Adc, I_C = 0)$	V _{(BR)EBO}	-6.0	-	Vdc
Collector Cutoff Current (V _{CE} = -250 Vdc)	I _{CES}	_	-10	nAdc
Emitter Cutoff Current (V _{EB} = -6.0 Vdc, I _C = 0)	I _{EBO}	-	0.1	μAdc
Collector Cutoff Current $ \begin{array}{l} (V_{CB}=-250 \text{ Vdc}, I_E=0, T_A=25^{\circ}\text{C}) \\ (V_{CB}=-250 \text{ Vdc}, I_E=0, T_A=100^{\circ}\text{C}) \end{array} $	I _{CBO}	- -	-0.005 -1.0	μAdc
ON CHARACTERISTICS	<u>.</u>			
DC Current Gain	h _{FE}	25 40	_ _	-
Collector – Emitter Saturation Voltage $(I_C = -20 \text{ mAdc}, I_B = -2.0 \text{ mAdc})$	V _{CE(sat)}	_	-2.0	Vdc
Base – Emitter On Voltage $(I_C = -20 \text{ mA}, I_B = -2.0 \text{ mA})$	V _{BE(sat)}	-	-2.0	Vdc
DYNAMIC CHARACTERISTICS	,		•	
Current – Gain – Bandwidth Product $(I_C = -10 \text{ mAdc}, V_{CE} = -20 \text{ Vdc}, f = 20 \text{ MHz})$	f _T	50	-	MHz
Common–Emitter Feedback Capacitance (V _{CB} = -100 Vdc, I _E = 0, f = 1.0 MHz)	C _{re}	_	1.6	pF

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu s$; Duty Cycle $\leq 2.0\%$.

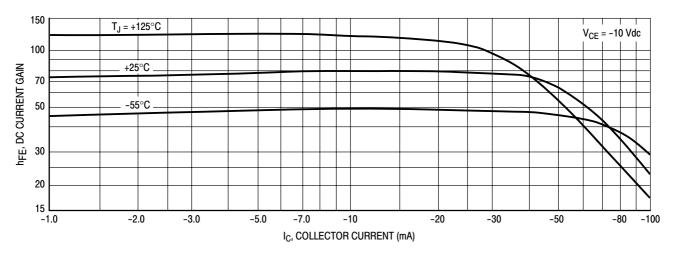


Figure 1. DC Current Gain

BF493S

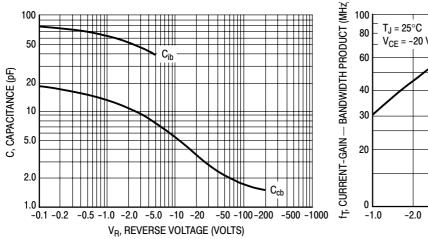


Figure 2. Capacitances

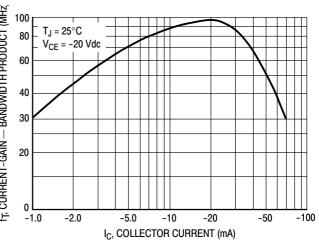


Figure 3. Current-Gain — Bandwidth Product

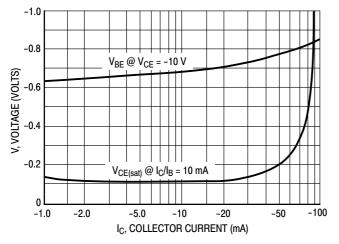


Figure 4. "On" Voltages

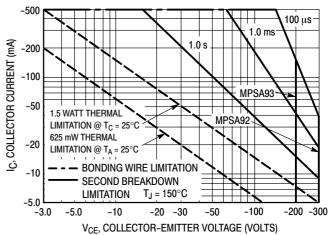
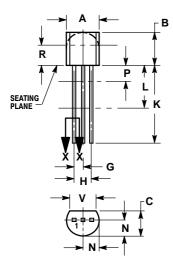


Figure 5. Active Region — Safe Operating Area

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



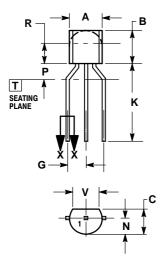
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

PIN 1. EMITTER

BASE

COLLECTOR

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